

Dear customer,

Please note that indicated dates are **gds-in deadlines**. If you want to participate onto one of below listed shuttles, please make sure to notify us about 4 weeks before this date to ensure a seat is reserved for you. You can send your notification mail to :

For tsmc technologies : eptsmc@imec.be

For umc technologies : epumc@imec.be

For xfab technologies : epxfab@imec.be

For ON Semiconductor technologies : greta.milczanowska@imec.be

For ams technologies :

If your service center is imec : ams_support@imec.be

If your service center is fraunhofer : virtual-asic@iis.fraunhofer.de

ON Semiconductor (formerly AMIS)

	J	F	M	A	M	J	J	A	S	O	N	D
ON Semi 0.7µ C07M-D 2M/1P & ON Semi 0.7µ C07M-A 2M/1P/Pdiff/HR	16		27			5		14		30		
ON Semi 0.35µ C035U - 4M (3M & 5M optional) only thick top metal	30			17			3		18			4
ON Semi 0.7µ C07M-I2T100 100 V - 2M & 3M options	16		27			5		14		30		
ON Semi 0.35µ C035 - I3T80U 80 V 4M - 3M optional (5M on special request)	2			3			10			9		
ON Semi 0.35µ C035 - I3T50U 50 V 4M - 3M optional (5M on special request)			6		29				4			4
ON Semi 0.35µ C035 - I3T50U (E) 50 V 4M - 3M optional (5M on special request)			6		29				4			4
ON Semi 0.35µ C035 - I3T25U 3.3/25 V 4M (3M & 5M optional) only thick top metal	30			17			3		18			4
ONC18MS (0.18 µm - 1.8/3.3 V - 15V DMOS - 5LM - MiMC - ESD - HiR - EPI)		6		10		12		16		10		11
ONC18MS-LL (=ONC18MS + High Vt)		6		10		12		16		10		11
ONC18HPA (= ONC18MS + DNW + Zener + Stacked MiMC + Native Dev + Schottky)		6		10		12		16		10		11
ONC18-I4T 45/70V HV CMOS (=ONC18MS + 30V + 45V + 70V DMOS)		6		10		12		16		10		11
ON Semi 0.5µ CMOS EEPROM C5F & C5N - 200 mm		2			3			3			16	

ams

	J	F	M	A	M	J	J	A	S	O	N	D
ams 0.35µ CMOS C35B4C3 4M/2P/HR/5V IO	30			24		12		7	25		20	
ams 0.35µ CMOS C35OPTO 4M/2P/5V IO				24				7			20	
ams 0.35µ HV CMOS H35B4D3 120V 4M		13			2			14		30		
ams 0.35µ SiGe-BiCMOS S35 4M/4P		27				6			11			11
ams 0.18µ CMOS aC18 6M/1P/MIM/1.8V/5V		20			22			21			27	
ams 0.18µ HV CMOS aH18 50V/20V/5V/1.8V/6M/MIM		20			22			21			27	
Bottom Anti Reflective Coating (BARC) Diode for ams 0.35µ CMOS C35OPTO 4M/2P/5V IO				24				7			20	
Wafer Level Chip Scale Package for ams 0.35µ CMOS C35B4C3 4M/2P/HR/5V IO				24				7			20	

Note: Customers making use of WLSCP have to send in their design gds file two weeks before the indicated deadline

IHP

	J	F	M	A	M	J	J	A	S	O	N	D
IHP SGB25V 0.25µ SiGe:C Ft=75GHz@BVCEO 2.4V				21				4				
IHP SG25H3 0.25µ SiGe:C Ft/Fmax= 110/180GHz 5M/MIM	30							4				
IHP SG25H4 0.25µ SiGe:C Ft/Fmax= 200/220GHz 5M/MIM	30			21				4				
SG25H_EPIC (based on SG25H4)										20		
IHP SG13S SiGe:C Bipolar/Analog/CMOS/RF-MEMS Ft/Fmax= 250/300GHz 7M/MIM			17					18			24	
IHP SG13C SiGe:C CMOS 7M/MIM			17					18			24	
IHP SG13G2 SiGe:C Bipolar/Analog/RF-MEMS Ft/Fmax= 300/500GHz 7M/MIM			17					18			24	
IHP SG25 PIC (Photonics, Ge Photo-diode, BEOL)				7								
IHP BEOL SG25 (M1 and Metal Layers Above) + LBE				7								
IHP BEOL SG13 (M1 and Metal Layers Above) + RF-MEMS + LBE + Cu						16						

Bumping available for all IHP technologies with extra charge, limited to 200 bumps

Important note: Dates are registration deadlines after which designs cannot enter this MPW run anymore. Final GDSII file must be submitted within 10 days after this date.

X-FAB

	J	F	M	A	M	J	J	A	S	O	N	D
XH018 0.18µ HV NVM CMOS E-FLASH *				24			31			30		
XT018 0.18µ HV SOI CMOS **	23		13		15		17		18			
XS018 0.18µ OPTO***		27						28				

* Process modules included for metal 4 option : LPMOS, MET3, METMID, MRPOLY, ISOMOS, LVT, DMOS, HVMOS, SCHOTTKY, MIM, NVM, FLASH, OTP3, PHOTODIO.

Process modules included for metal 6 option : LPMOS, MET3, MET4, METMID, METTHK, MRPOLY, ISOMOS, LVT, DMOS, HVMOS, SCHOTTKY, MIM, NVM, FLASH, OTP3, PHOTODIO.

** Process modules included for metal 4 option: LP5MOS, HVN, HVP, 1XN, 1XP, PSUB, DTI, DNC, DPC, NBUR, HRPOLY, MIMH, MET3, METTHK, HWC.

Process modules included for metal 6 option : LP5MOS, HVN, HVP, 1XN, 1XP, PSUB, DTI, DNC, DPC, NBUR, HRPOLY, MIMH, MET3, MET4, METMID, METTHK, HWC.

*** Process modules included for metal 4 option: MOS3LP, MOSLP, METTHIN, MET3, MET4, MRPOLY, ISOMOS, LVTN3D, BCH, MIM23, PPDB, 4TPIX, SFLATPV.

Process modules included for metal 6 option : MOS3LP, MOSLP, MET3, MET4, MET5, METMID, MRPOLY, ISOMOS, LVTN3D, BCH, MIM23, PPDB, 4TPIX, SFLATPV.

TSMC

	J	F	M	A	M	J	J	A	S	O	N	D
TSMC 0.18 CMOS Logic or Mixed-Signal/RF, General	3,25	7,22	1,29	12,26	9,24	7,21	12,26	9,23	6	4,17, 25	8,22 29	
TSMC 0.18 CMOS High Voltage BCD Gen Generation 2		7,22	1,29	12	3	7,22	12	9,23, 30		4,17	1,29	
TSMC 0.13 CMOS Logic or Mixed-Signal/RF, General or Low Power (8-inch)		7	14		9	14	26		6		1,22	
TSMC 0.13 CMOS Logic or Mixed-Signal/RF, General or Low Power (12-inch)				12			12		27			
TSMC 90nm CMOS Logic or Mixed-Signal/RF, General or Low Power			1	26		28			6		1	
TSMC 65nm CMOS LP or Mixed-Signal/RF, General	3	1,22		5,26	31		5	2,30	27	25	29	
TSMC 40nm CMOS LP or Mixed-Signal/RF, General (no triple gate oxide)	25	15	29	19	24	21	26	23	27	25	22	
TSMC 28nm CMOS Logic, HPL/HPC, RF HPL/HPC (reserve 4 months in advance)		1	1	5	3	7	5	2	6	4	1	6

UMC

	J	F	M	A	M	J	J	A	S	O	N	D
UMC L180 Logic GII, Mixed-Mode/RF	30		27			5	24			2		4
UMC L180 EFLASH Logic GII ⁽¹⁾		6							4			
UMC CIS180 Image Sensor 1P4M - CONV diode ⁽¹⁾			27							10		
UMC CIS180 Image Sensor 2P4M - ULTRA diode ⁽¹⁾			27							10		
UMC L130 Logic/ Mixed-Mode/RF			6			26					6	
UMC L110AE Logic/Mixed-Mode/RF	9	27		24	8	19		28		30		11
UMC L65N Logic/Mixed-Mode/RF - LL		6		3*	22	19*	31		18*	30		11
UMC L65N Logic/Mixed-Mode/RF - SP		6		3*	22	19*	31		18*	30		11
UMC 55N EFLASH EEPROM LP SPLIT GATE				3		19			18			11
UMC 40N Logic/Mixed-Mode - LP		27				12	3	14	25	23		
UMC 28N Logic/ Mixed-Mode - HPC ⁽¹⁾		21				12			11		27	

Run has been cancelled by UMC.

options regular runs	Core	IO	MIM	topmetal	special remarks
UMC L180 Logic GII	1.8V	3.3V	1fF	8kA - Max. 1P6M	Redistribution and bumping on request
UMC L180 Mixed-Mode/RF	1.8V	3.3V	1fF	8kA/20kA Max. 1P6M	Redistribution and bumping on request.
UMC L180 EFLASH logic GII	1.8V	3.3V	/	8kA - Max. 2P6M	Please get in touch with imec for the EFLASH macro information.
UMC CIS18 - CONV	1.8V	3.3V	1fF	5kA - Max.1P4M	Colorfilters and microlenses included
UMC CIS18 - ULTRA	1.8V	3.3V	1fF	5kA - Max.2P4M	Colorfilters and microlenses included. Ultra diode is pinned. PIP capacitor possible.
UMC L130 Logic	1.2V	3.3V	1fF/1.5fF/2fF	8kA Max. 1P8M2T	Two types (out of 3) of devices can be combined: HS,LL, SP. Redistr. to Al.
UMC L130 Mixed-Mode/RF	1.2V	3.3V	1fF/1.5fF/2fF	8kA/20kA Max. 1P8M2T	Two types (out of 3) of devices can be combined: HS,LL, SP. Redistr. to Al.
UMC L110AE Logic/Mixed-Mode/RF	1.2V	1.8V/2.5V/3.3V/5V	1fF/1.5fF/2fF	8kA/12kA/20kA/40kA Max. 1P8M	Metallization is Aluminium. 5V device possible! HS,LL,SP can be combined.
UMC L65N Logic/Mixed-Mode/RF - SP	1.0V, 1.1V	1.8V/2.5V/ 2.5V_OD3.3V/3.3V	2fF	8kA/32.5kA Max. 1P10M	Metallization recommendation on request. Redistribution to Aluminium. * = 32kA topmetal, LVT, MIM in development. 2.5V_OD3.3V not available. ** = 3.3V not available. Please check with us before tapeout.
UMC L65N Logic/Mixed-Mode/RF - LL	1.2V	1.8V/2.5V/ 2.5V_OD3.3V/3.3V	2fF	8kA/32.5kA Max. 1P10M	Metallization recommendation on request. Redistribution to Aluminium. * = 32kA topmetal in development. Please check with us before tapeout.
UMC 55N EFLASH EEPROM LP SPLIT GATE	1.2V	2.5V	2fF	8kA	Metallization recommendation on request. Redistribution to Aluminium.
UMC 40N Logic/Mixed-Mode - LP	0.9V	1.8V/2.5V	2fF	8kA/12kA/32.5kA	Metallization recommendation on request. Redistribution to Aluminium.
UMC 28N Logic/Mixed-Mode - HPC	1.0 & 1.1V	1.8V/2.5V	2fF	8kA/12kA/32.5kA	Metallization recommendation on request. Redistribution to Aluminium.

(1) Contact Europractice when planning to participate to those runs.

GLOBALFOUNDRIES

	J	F	M	A	M	J	J	A	S	O	N	D
GLOBALFOUNDRIES 55 nm LPe/LPx-NVM/LPx-RF	9		13		15		17		18		13	
GLOBALFOUNDRIES 40 nm LP/LP-RF/RF-mmWave	30			3		6	31			2		4
GLOBALFOUNDRIES 28 nm SLP/SLP-RF		6			8			7			6	
GLOBALFOUNDRIES 22 nm FDSOI		13		18	22	12	10	28	25	16	13	11

Important note: Dates are registration deadlines after which designs cannot enter this MPW run anymore. Final GDSII file must be submitted within 6 weeks after this date.

MEMSCAP

	J	F	M	A	M	J	J	A	S	O	N	D
PolyMUMPS			21			22			19			
SOIMUMPS		22			23			24			22	
PIEZOMUMPS					9			29				

ePIXfab-imec

	J	F	M	A	M	J	J	A	S	O	N	D
ePIXfab-imec SiPhotonics Passives			15						15			
ePIXfab-imec SiPhotonics iSiPP50G					5					20		

* iSiPP50G = advanced passives + Modulator + Detector + LPASS + M2 + edge coupler

ePIXfab-LETI

	J	F	M	A	M	J	J	A	S	O	N	D
ePIXfab-LETI SiPhotonics Passives		20						28				
ePIXfab-LETI SiPhotonics Passives with Heater		20						28				

Teledyne Dalsa

	J	F	M	A	M	J	J	A	S	O	N	D
Teledyne Dalsa MIDIS										15		

2017 General Europractice MPW runs – Pricelist

Prices are valid for MPW runs starting after 1 January 2017

Accessible for universities, research institutes and companies
Prices and conditions may change at any time without prior notice

STANDARD price : normal price

DISCOUNTED price : only applies to EURO PRACTICE registered (who paid their annual full membership fee) Academic and Research Members from all 28 EU countries and Albania, Armenia, Azerbaijan, Belarus, Bosnia-Herzegovina, Georgia, Iceland, Israel, Liechtenstein, Former Yugoslav Republic of Macedonia, Moldova, Montenegro, Norway, Russia, Switzerland, Turkey, Serbia and Ukraine who submit designs for **educational or publicly funded research use only**

Prices are given for the delivery of unpackaged, untested prototypes. Encapsulation and testing will be charged separately.

Number of prototypes

OnSemi, XFAB : 30 samples
ams , IHP : 40 samples
UMC : 0.18um, 0.13um, 0.11um : 50 samples
UMC : 65nm : 90 samples
TSMC : 8-inch : 40 samples, 12-inch : 100 samples
Imec SiPhotonics passives :25 samples, ISIPP25G+ : 20 samples
miniphotonics : 10 samples
MEMSCAP : 15 samples
GLOBALFOUNDRIES : 50 samples
If you need more prototype samples, please ask for a quotation

Plots

You can order plots/PDF of your designs
- first plot/PDF costs 50 euro
- next plots cost 20 euro each

Packaging : see separate prices and available packages

PRICES IN EURO

ams	STANDARD Price/mm ²	DISCOUNTED Price/mm ²
ams 0.35µ CMOS C35B4C3 4M/2P/HR/5V IO	640 ⁴	580 ⁴
ams 0.35µ CMOS C35OPTO 4M/2P/5V IO	800 ⁴	700 ⁴
ams 0.35µ HV CMOS H35B4D3 120V 4M	880 ⁴	800 ⁴
ams 0.35µ SiGe-BiCMOS S35 4M/4P	880 ⁴	800 ⁴
ams 0.18µ CMOS aC18 6M/1P/MIM/1.8V/5V	1100 ⁴	1050 ⁴
ams 0.18µ HV CMOS aH18 6M/50V/20V/5V/1.8V/MIM	1150 ⁴	1100 ⁴
BARC Diode for ams 0.35µ CMOS C35OPTO 4M/2P/5V IO	One-off fee of 13800	One-off fee of 13800
Wafer Level Chip Scale Package for ams 0.35µ CMOS C35B4C3	One-off fee of 6450	One-off fee of 6150

ON Semiconductor (formerly AMIS)	STANDARD Price/mm²	DISCOUNTED Price/mm²
ON Semi 0.7μ C07M-D 2M/1P	300 ²	270 ²
ON Semi 0.7μ C07M-A 2M/1P/PdiffC/HR	350 ²	315 ²
ON Semi 0.5μ CMOS EEPROM C5F & C5N – 200 mm	1150 ²	1100 ²
ON Semi 0.7μ C07M-I2T100 100 V - 2M	525 ¹	485 ¹
ON Semi 0.7μ C07M-I2T100 100 V - 3M	560 ¹	525 ¹
ON Semi 0.35μ C035U 4M (default) including analog options	720 ¹	670 ¹
ON Semi 0.35μ C035U 3M (optional) including analog options	700 ¹	650 ¹
ON Semi 0.35μ C035U 5M (optional) including analog options	800 ¹	750 ¹
ON Semi 0.35μ C035 - I3T80U 80 V 3M	850 ¹	800 ¹
ON Semi 0.35μ C035 - I3T80U 80 V 4M	925 ¹	875 ¹
ON Semi 0.35μ C035 - I3T80U 80 V 5M	1050 ¹	995 ¹
ON Semi 0.35μ C035 - I3T50U (or E) 50 V 3M	850 ¹	800 ¹
ON Semi 0.35μ C035 - I3T50U (or E) 50 V 4M	925 ¹	875 ¹
ON Semi 0.35μ C035 - I3T50U (or E) 50 V 5M	1050 ¹	995 ¹
ON Semi 0.35μ C035 - I3T25U 3.3/25 V 3M (optional)	750 ¹	700 ¹
ON Semi 0.35μ C035 - I3T25U 3.3/25 V 4M (default)	770 ¹	720 ¹
ON Semi 0.35μ C035 - I3T25U 3.3/25 V 5M (optional)	800 ¹	750 ¹
ONC18MS 0.18 μm - 1.8/3.3 V - 15V DMOS - 5LM - MiMC - ESD - HiR - EPI	1,100 ¹	1,050 ¹
ONC18MS-LL (=ONC18MS + High Vt)	1,225 ¹	1,195 ¹
ONC18HPA (= ONC18MS + DNW + Zener + Stacked MiMC + Native Dev + Schottky)	1,350 ¹	1,290 ¹
ON 0.18 μm I4T 40/75 V - 5LM - DTI (=ONC18MS + 30V + 45V + 70V DMOS)	1,540 ¹	1,480 ¹

IHP	STANDARD Price/mm²	DISCOUNTED Price/mm²
IHP SGB25V 0.25μ SiGe:C Ft=75GHz@BVCEO 2.4V	2500 ⁸	1940 ⁸
IHP SG25H3 0.25μ SiGe:C Ft/Fmax= 110/180GHz 5M/MIM	3800 ⁸	2950 ⁸
IHP SG25H4 0.25μ SiGe:C Ft/Fmax= 200/220GHz 5M/MIM	4600 ⁸	3220 ⁸
SG25H_EPIC (based on SG25H4)	6600 ⁸	3960 ⁸
IHP SG13G2 SiGe:C Bipolar/Analog Ft/Fmax= 300/500GHz 7M/MIM	7300 ⁸	5110 ⁸
IHP SG13S SiGe:C Bipolar/Analog/CMOS Ft/Fmax= 250/300GHz 7M/MIM	6300 ⁸	4410 ⁸
IHP SG13C SiGe:C CMOS 7M/MIM	4500 ⁸	3375 ⁸
BEOL SG25 (M1 and Metal Layers Above, for passive structures)	800 ⁸	640 ⁸
BEOL SG13 (M1 and Metal Layers Above, for passive structures)	1000 ⁸	800 ⁸
IHP SG25 PIC (Photonics devices, Ge Photo-diode, BEOL)	2000 ⁸	1200 ⁸
bumping (available for all IHP technologies)	One-off fee of 6500 ⁹	One-off fee of 4700 ⁹
localized back side etching (available for all IHP technologies)	One-off fee of 5000	One-off fee of 2500
RF-MEMS switch for SG13 (IP)	One-off fee of 10000	One-off fee of 2500
TSV to ground (SG25H4)	One-off fee of 5000	One-off fee of 2500

X-FAB	STANDARD Price/mm²	DISCOUNTED Price/mm²
X-FAB XH018 0.18μ HV NVM CMOS E-FLASH (MET3, METMID)	1430 ^{1,11}	1360 ^{1,11}
X-FAB XH018 0.18μ HV NVM CMOS E-FLASH (MET3, MET4, METMID, METTHK)	1580 ^{1,11}	1505 ^{1,11}
X-FAB XT018 0.18μ HV SOI CMOS (MET3, METTHK)	1440 ^{1,11}	1365 ^{1,11}
X-FAB XT018 0.18μ HV SOI CMOS (MET3, MET4, METMID, METTHK)	1615 ^{1,11}	1535 ^{1,11}
XS018 0.18μ OPTO (METTHIN, MET3, MET4)	1205 ^{1,11}	1145 ^{1,11}
XS018 0.18μ OPTO (MET3, MET4, MET5, METMID)	1355 ^{1,11}	1290 ^{1,11}

TSMC	STANDARD Price/mm²	DISCOUNTED Price/mm²
All TSMC technologies	Upon request ⁷	Upon request ⁷

UMC	STANDARD Price/block	DISCOUNTED Price/block
UMC L180 Logic GII, Mixed-Mode/RF	15600 ⁵	14820 ⁵
UMC L180 CIS 1P4M CONV or 2P4M ULTRA	24600 ⁵	23380 ⁵
UMC L180 EFLASH Logic GII	19500 ⁵	18540 ⁵
UMC L130 Logic/Mixed-Mode/RF	26250 ⁵	24940 ⁵
UMC L110AE Logic/Mixed-Mode/RF	28850 ⁵	27420 ⁵
UMC 65nm Logic, Mixed-Mode/ RF - LL/SP	41850 ⁶	39760 ⁶
UMC 55N EFLASH EEPROM LP SPLIT GATE	44250 ⁶	42040 ⁶
UMC 40N Logic/Mixed-Mode - LP	78750 ⁶	74820 ⁶
UMC 28N Logic/ Mixed-Mode - HPC	Upon request, please contact EP	

GLOBALFOUNDRIES	STANDARD Price/mm²	DISCOUNTED Price/mm²
GLOBALFOUNDRIES 55 nm LPx-NVM/LPx-RF	4000 ¹²	3800 ¹²
GLOBALFOUNDRIES 55 nm LPe	4000 ¹²	3800 ¹²
GLOBALFOUNDRIES 40 nm LP/LP-RF/RF-mmWave	5000 ¹²	4700 ¹²
GLOBALFOUNDRIES 28 nm SLP-RF	10200 ¹²	9700 ¹²
GLOBALFOUNDRIES 22 nm FDX FDSOI	14700 ¹²	14000 ¹²

MEMSCAP	STANDARD Price/block	DISCOUNTED Price/block
PolyMUMPS, SOIMUMPS, PIEZOMUMPS - 10x10mm ¹⁰	4200	3990

Optional Postprocessing : see pricelist on www.europactice-ic.com

		Minimal size dies (die size design size)		Larger size dies or undiced wafer (die = design + cleared perimeter)		Un-diced 200mm wafer	
		STANDARD Price	DISCOUNTED Price	STANDARD Price	DISCOUNTED Price	STANDARD Price	DISCOUNTED Price
ePIXfab-imec SiPhotonics Passives							
1 block	6 x 3 mm	5000	4750	7400	7150	7400	7150
2 blocks - vertical	6 x 6.2 mm	9500	9000	11900	11400	11900	11400
2 blocks - horizontal	12.2 x 3 mm	9500	9000	11900	11400	11900	11400
4 blocks	12.2 x 6.2 mm	17000	16200	19400	18600	19400	18600
25 additional compact dies		+1000	+1000	+1000	+1000	+1000	+1000
25 additional large dies		NA	NA	+2000	+2000	+2000	+2000
1 additional un-diced 200mm wafer		NA	NA	+2000	+2000	+2000	+2000
Cladding		Included	Included	Included	Included	Included	Included
High dose WG		+1000	+1000	+1000	+1000	+1000	+1000

		STANDARD Price	DISCOUNTED Price
ePIXfab-imec SiPhotonics ISSIP50G			
miniPhotonics (10 samples)	2.5 mm x 2.5 mm	10000	9500
	5.15 mm x 2.5 mm	20000	19000
Regular (20 samples)	5.15 mm x 5.15 mm	40000	38000
	10.45 mm x 5.15 mm	80000	76000
	10.45 mm x 10.45 mm	150000	142500
20 additional dies		+1000	+1000

		Minimum area : 2 full blocks		Minimum area : 5 full blocks	
		STANDARD Price	DISCOUNTED Price	STANDARD Price	DISCOUNTED Price
ePIXfab-LETI SiPhotonics Passives (if not enough designs LETI can cancel the run)					
Regular	Full : 6.0 x 4.0 mm	4870	4630	3230	3070
	Half : 6.0 x 2.0 mm	2435	2315	1615	1535
Larger sizes		Contact us	Contact us	Contact us	Contact us
Variable dose, metrology, dicing, fabrication report, final resist cladding		Included	Included	Included	Included
Deep rib 65nm		+1765			

		Minimum area : 2 full blocks		Minimum area : 5 full blocks	
		STANDARD Price	DISCOUNTED Price	STANDARD Price	DISCOUNTED Price
ePIXfab-LETI SiPhotonics Passives + heater + metallization for wire bonding compatibility (if not enough designs LETI can cancel the run)					
miniPhotonics (15 samples)	4.0 x 2.0 mm	9550	9075	NA	NA
	4.0 x 4.0 mm	19100	18145	NA	NA
Regular (25 samples)	Half : 6.0 x 2.0 mm	14325	13610	10750	10215
	Full : 6.0 x 4.0 mm	28650	27220	21500	20425
Larger sizes		Contact us	Contact us	Contact us	Contact us
Variable dose, metrology, dicing, fabrication report, final resist cladding		Included	Included	Included	Included
Deep rib 65nm		+1765			
Passivation opening		+1765			

		STANDARD Price	DISCOUNTED Price
Teledyne Dalsa (prices only for academia)			
MiDIS	4.0 mm x 4.0 mm	8000 Canadian dollar	NA
	4.0 mm x 8.0 mm	15400 Canadian dollar	NA
	8.0 mm x 8.0 mm	29800 Canadian dollar	NA

- Notes
- Price = area (mm²) * price/mm² with min. fabrication cost equivalent to 10 mm²
 - Price = area (mm²) * price/mm² with min. fabrication cost equivalent to 5 mm²
 - Price = area (mm²) * price/mm² with min. fabrication cost equivalent to 8 mm²
 - Price = area (mm²) * price/mm² with min. fabrication cost equivalent to 7 mm²
 - Price = per block of 5x5mm needed to fit the design in
 - Price = per block of 4x4mm needed to fit the design in
 - Price can be calculated through http://www.europractice-ic.com/TSMC_request_prices.php
 - Price = area (mm²) * price/mm² with min. fabrication cost equivalent to 0.8 mm²
 - Price = per submitted design (no size limit, bumping limited to 200 bumps)
 - Cost for extra services like structures release, subdicing, ... please refer to http://www.europractice-ic.com/MEMS_pricing.php
 - Area will be rounded upwards to the next mm² (eg. 12.24 mm² will be charged as 13 mm²)
 - Price = area (mm²) * price/mm² with min. fabrication cost equivalent to 9 mm²
Any edge length between 1.0 mm to 12.5 mm is possible. The mentioned die size is referred to the Pre-Shrink die size

Contacts

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